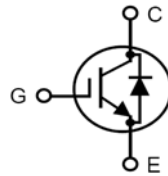
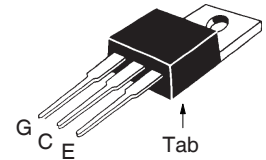


**XPT™ 650V IGBT
GenX3™ w/Diode**
IXYP20N65B3D1

 Extreme Light Punch Through
IGBT for 5-30kHz Switching


$$\begin{aligned} V_{CES} &= 650V \\ I_{C110} &= 20A \\ V_{CE(sat)} &\leq 2.10V \\ t_{fi(typ)} &= 87ns \end{aligned}$$

TO-220


 G = Gate C = Collector
E = Emitter Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 175°C	650	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 175°C , $R_{GE} = 1M\Omega$	650	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	58	A
I_{C110}	$T_C = 110^\circ\text{C}$	20	A
I_{F110}	$T_C = 110^\circ\text{C}$	23	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1ms	108	A
I_A	$T_C = 25^\circ\text{C}$	10	A
E_{AS}	$T_C = 25^\circ\text{C}$	200	mJ
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 150^\circ\text{C}$, $R_G = 20\Omega$ Clamped Inductive Load	$I_{CM} = 40$ @ $V_{CE} \leq V_{CES}$	A
t_{sc} (SCSOA)	$V_{GE} = 15V$, $V_{CE} = 360V$, $T_J = 150^\circ\text{C}$ $R_G = 82\Omega$, Non Repetitive	5	μs
P_C	$T_C = 25^\circ\text{C}$	230	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
M_d	Mounting Torque	1.13/10	Nm/lb.in.
Weight		3.0	g

Features

- Optimized for 5-30kHz Switching
- Square RBSOA
- Avalanche Rated
- Anti-Parallel Fast Diode
- Short Circuit Capability
- International Standard Package

Advantages

- High Power Density
- Extremely Rugged
- Low Gate Drive Requirement

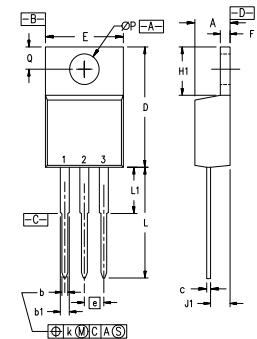
Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}$, $V_{GE} = 0V$	650		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}$, $V_{CE} = V_{GE}$	3.5		6.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 150^\circ\text{C}$			10 μA 400 μA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 20A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ\text{C}$	1.77 2.05		2.10 V V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 20\text{A}, V_{CE} = 10\text{V}$, Note 1	8.5	14	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		826	pF
C_{oes}			82	pF
C_{res}			19	pF
$Q_{g(on)}$	$I_C = 20\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		29	nC
Q_{ge}			6	nC
Q_{gc}			14	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 20\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 20\Omega$ Note 2		12	ns
t_{ri}			25	ns
E_{on}			0.50	mJ
$t_{d(off)}$			103	ns
t_{fi}			87	ns
E_{off}			0.45	mJ
$t_{d(on)}$	Inductive load, $T_J = 150^\circ\text{C}$ $I_C = 20\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 20\Omega$ Note 2		13	ns
t_{ri}			26	ns
E_{on}			0.93	mJ
$t_{d(off)}$			124	ns
t_{fi}			147	ns
E_{off}			0.76	mJ
R_{thJC}			0.65	$^\circ\text{C/W}$
R_{thCS}		0.50		$^\circ\text{C/W}$

TO-220 Outline



Pins: 1 - Gate 2 - Collector
3 - Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
$\varnothing P$.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

Reverse Diode (FRED)

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
V_F	$I_F = 20\text{A}, V_{GE} = 0\text{V}$, Note 1 $T_J = 150^\circ\text{C}$		1.2	2.5 V
I_{RM}	$I_F = 20\text{A}, V_{GE} = 0\text{V},$ $-di_F/dt = 300\text{A}/\mu\text{s}, V_R = 400\text{V}, T_J = 150^\circ\text{C}$		11	A
t_{rr}			134	ns
R_{thJC}				1.85 $^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher V_{CE} (clamp), T_J or R_G .

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

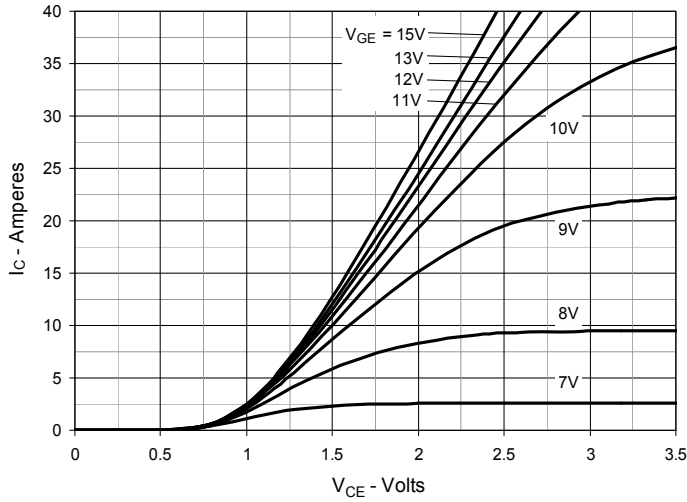
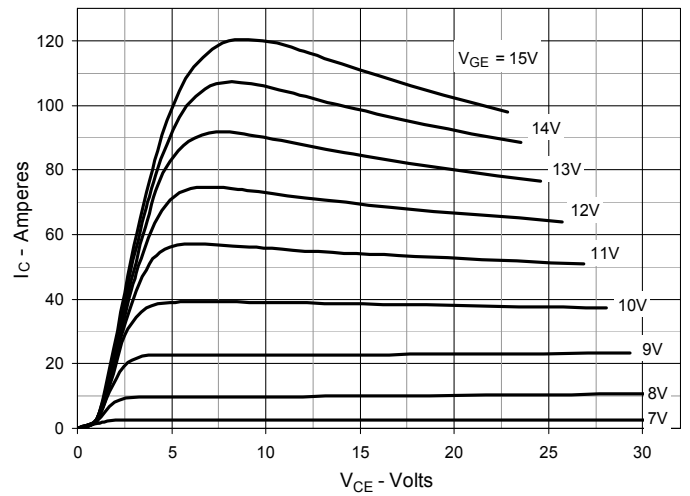
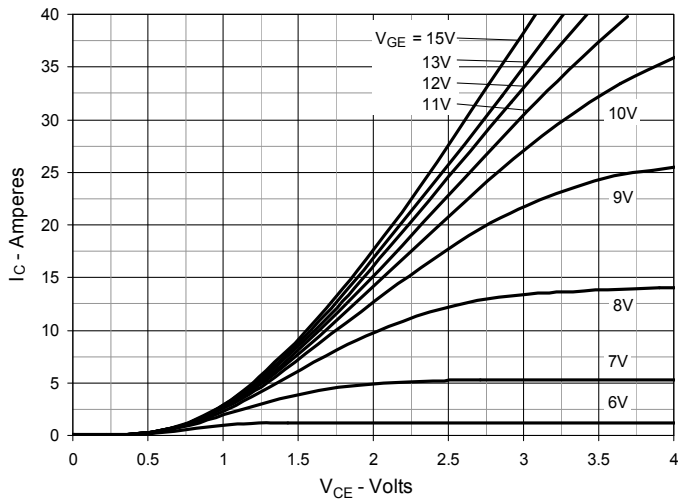
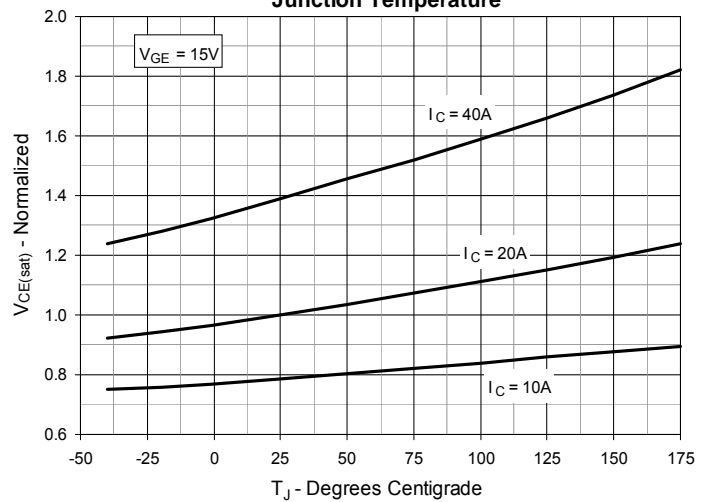
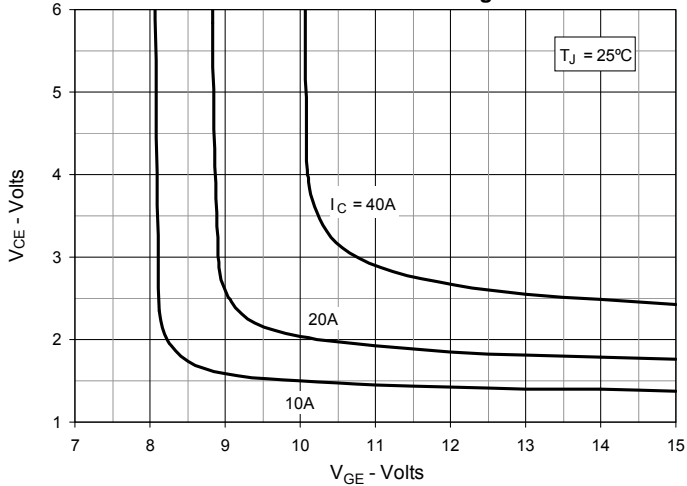
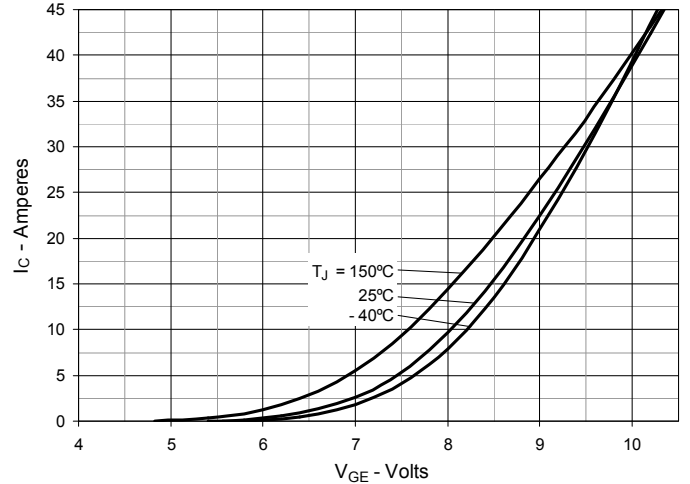
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


Fig. 7. Transconductance

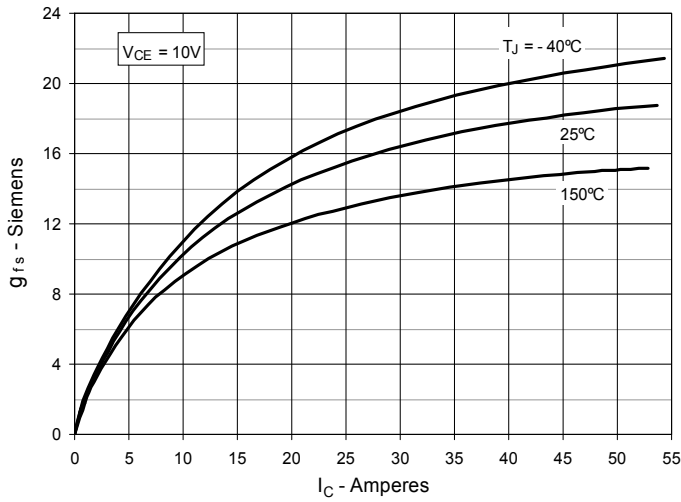


Fig. 8. Gate Charge

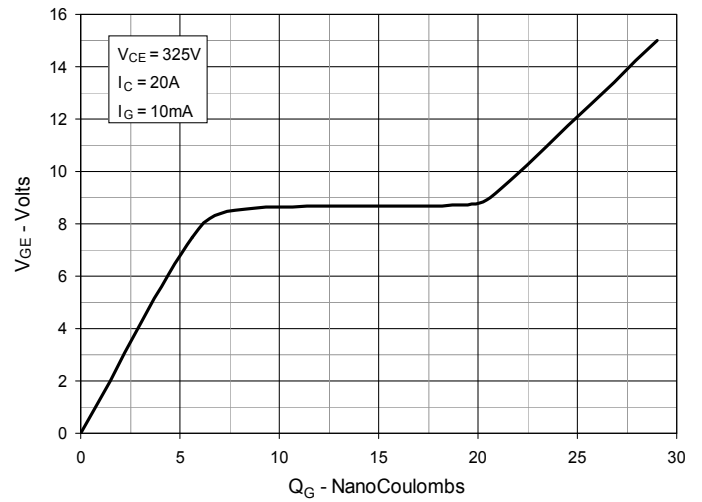


Fig. 9. Capacitance

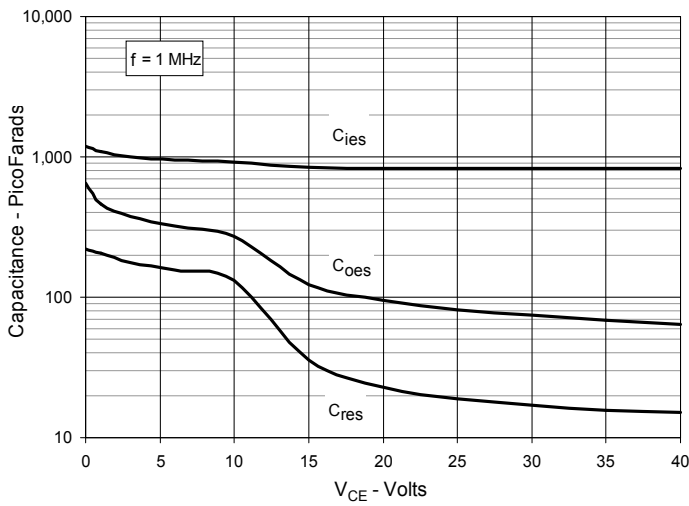


Fig. 10. Reverse-Bias Safe Operating Area

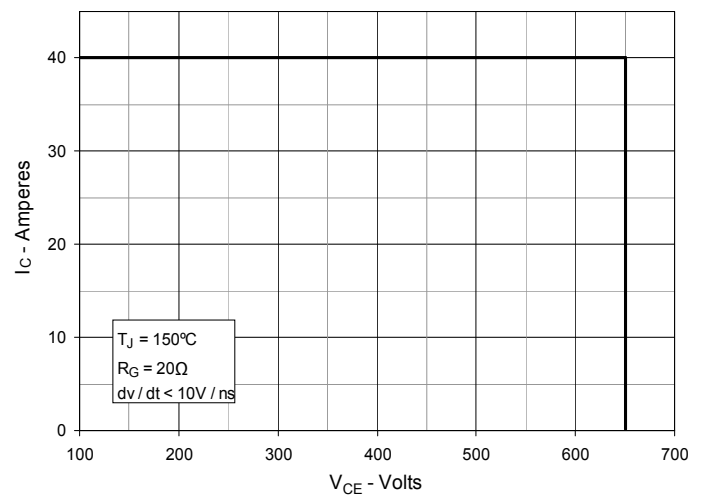


Fig. 11. Forward-Bias Safe Operating Area

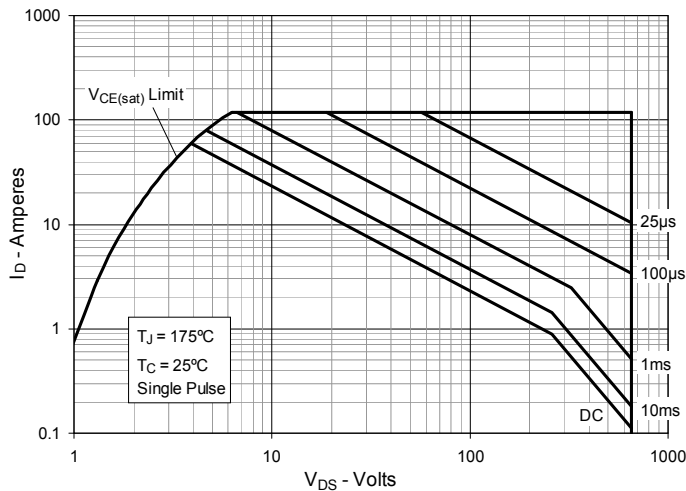


Fig. 12. Maximum Transient Thermal Impedance (IGBT)

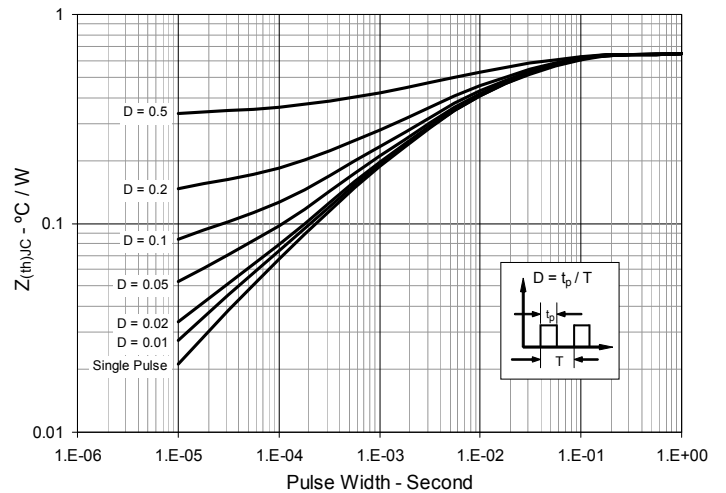


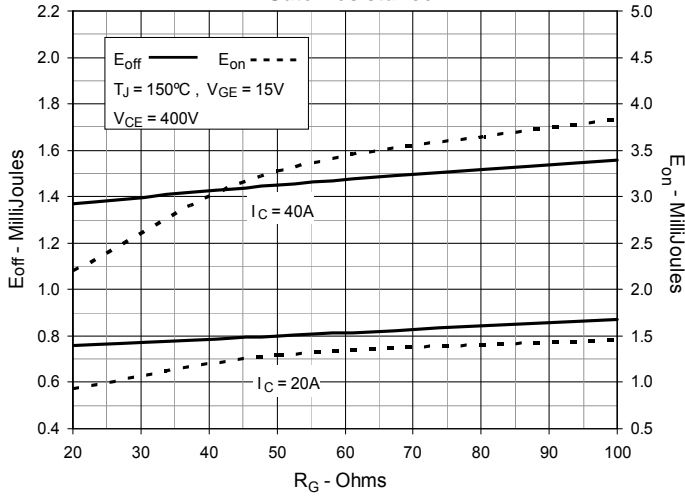
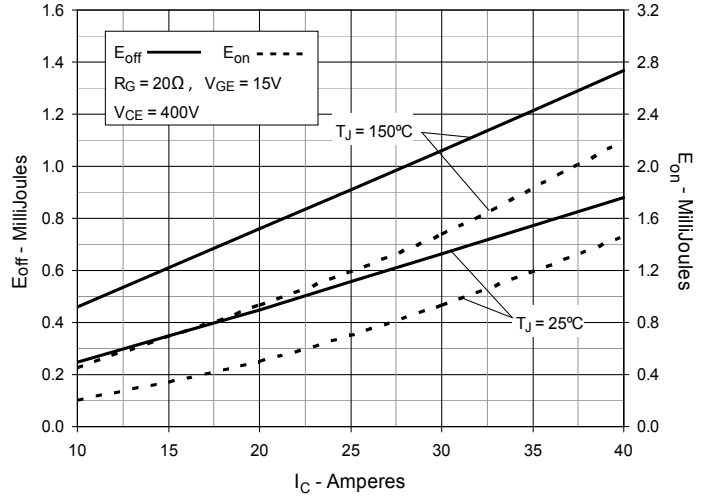
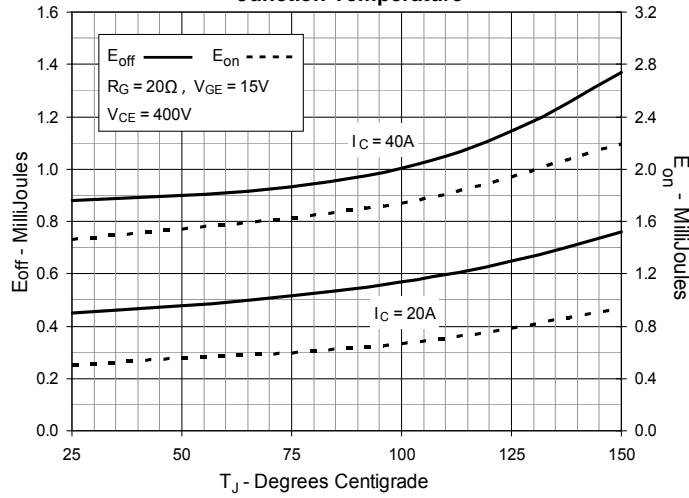
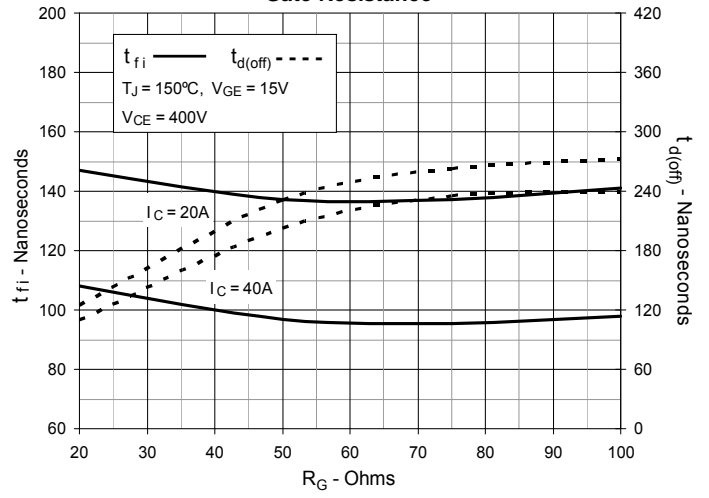
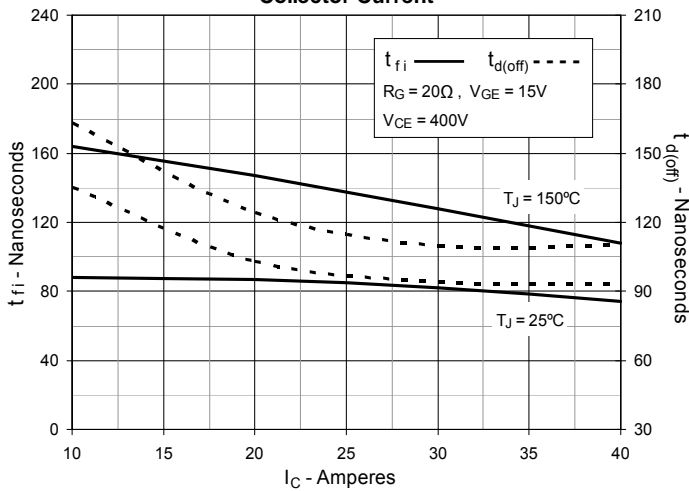
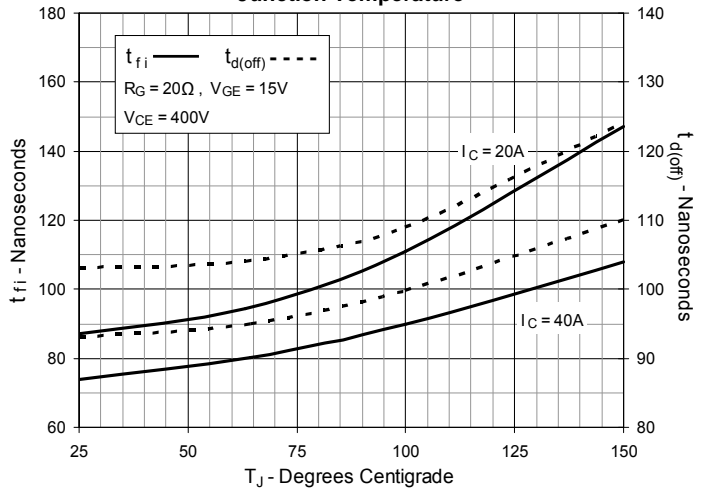
Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance

Fig. 14. Inductive Switching Energy Loss vs. Collector Current

Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature

Fig. 16. Inductive Turn-off Switching Times vs. Gate Resistance

Fig. 17. Inductive Turn-off Switching Times vs. Collector Current

Fig. 18. Inductive Turn-off Switching Times vs. Junction Temperature


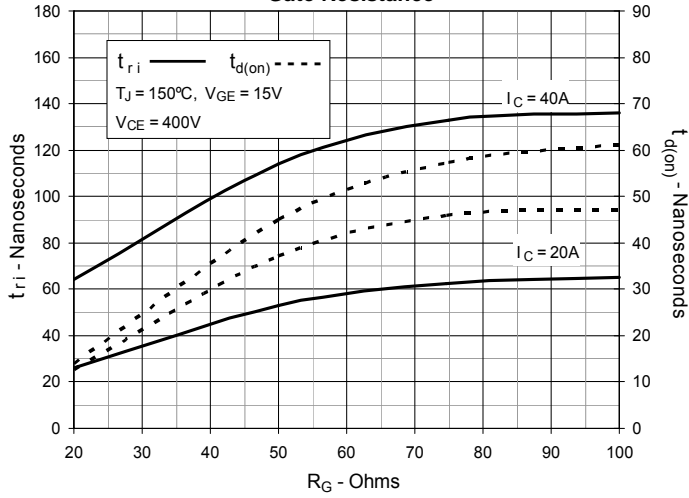
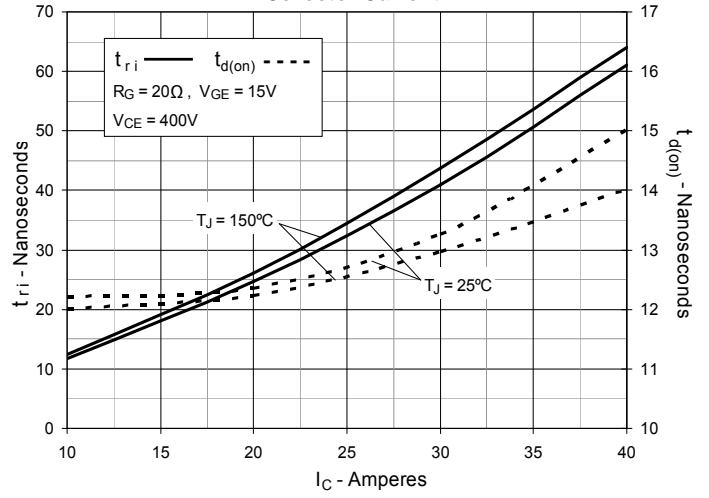
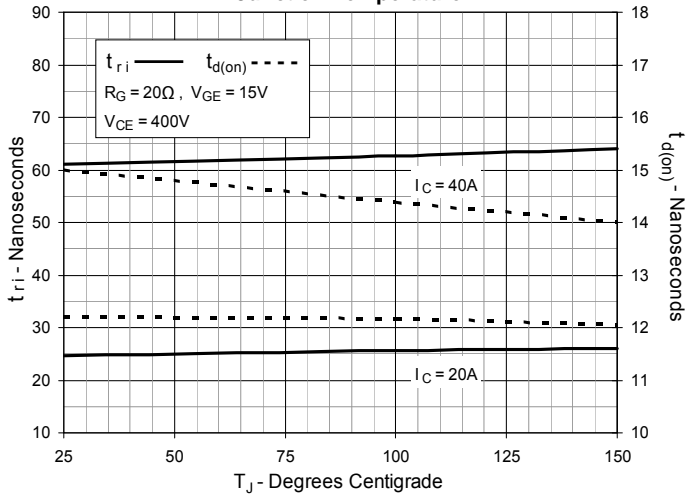
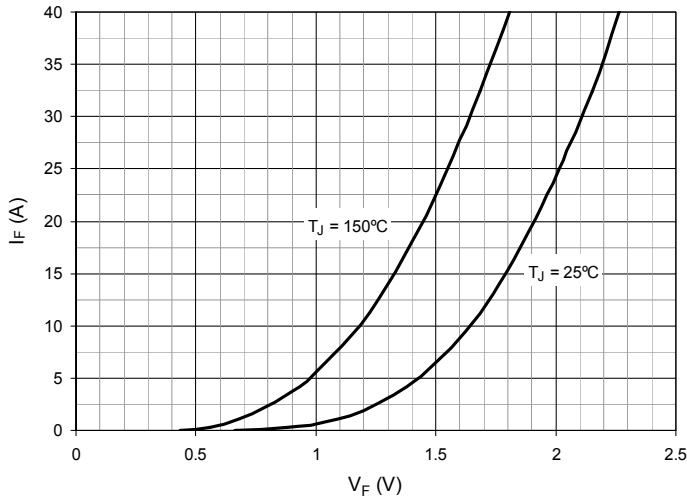
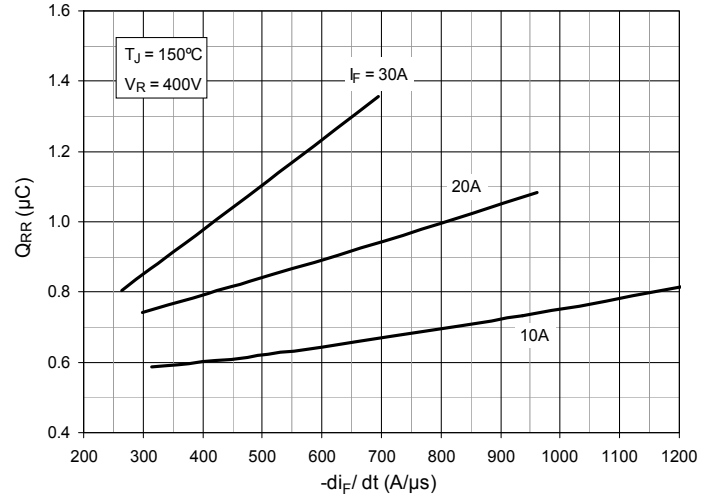
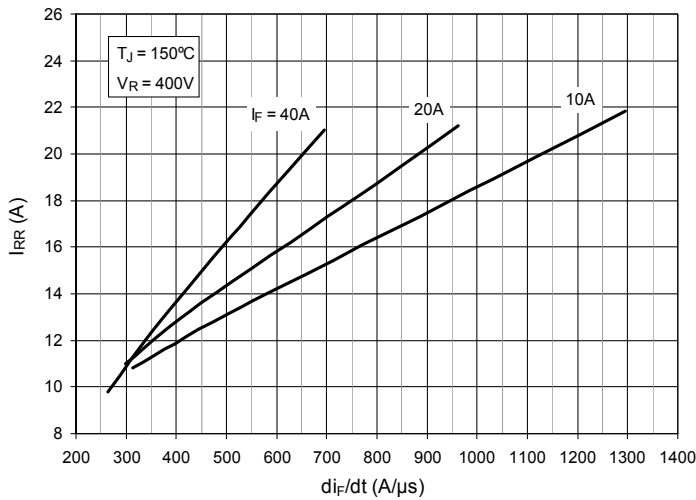
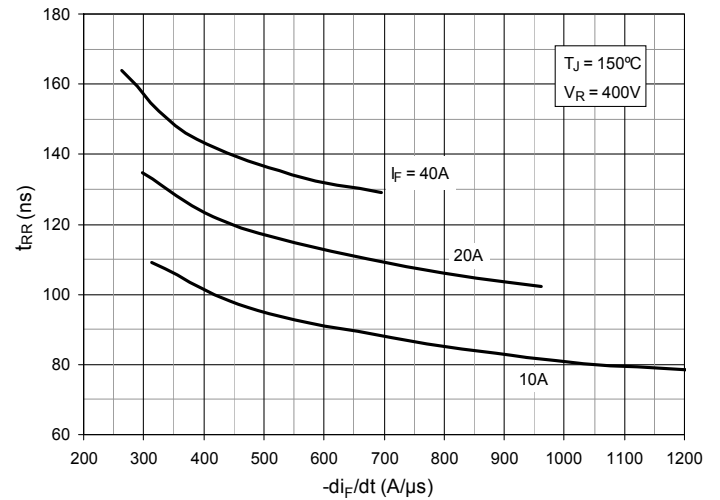
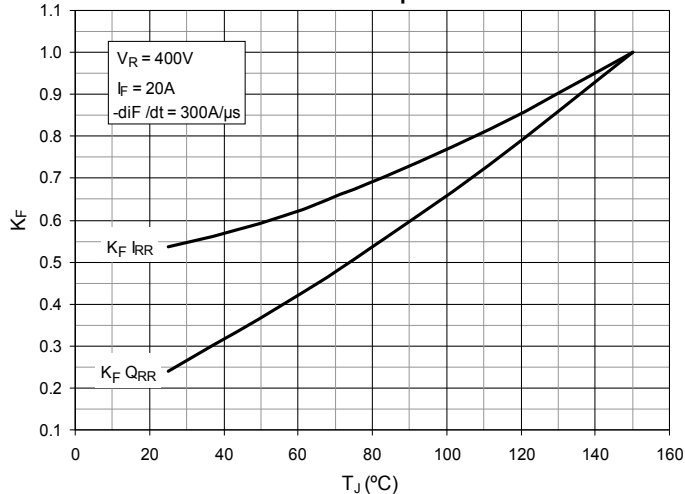
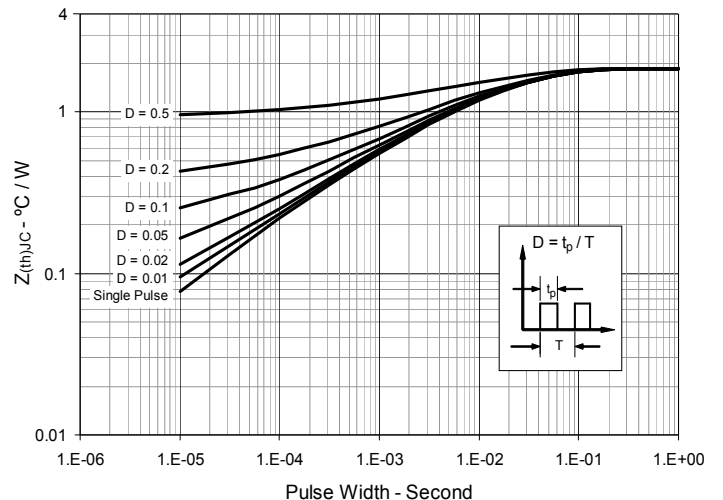
Fig. 19. Inductive Turn-on Switching Times vs. Gate Resistance

Fig. 20. Inductive Turn-on Switching Times vs. Collector Current

Fig. 21. Inductive Turn-on Switching Times vs. Junction Temperature


Fig. 22. Diode Forward Characteristics

Fig. 23. Reverse Recovery Charge vs. $-di_F/dt$

Fig. 24 Reverse Recovery Current vs. $-di_F/dt$

Fig. 25. Reverse Recovery Time vs. $-di_F/dt$

Fig. 26. Dynamic Parameters Q_{RR} , I_{RR} vs. Junction Temperature

Fig. 27. Maximum Transient Thermal Impedance (Diode)




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